

Nobuhiko Mitoma

List of Publications by Year in descending order

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Version: 2024-02-01

24
papers

691
citations

686830

13
h-index

610482

24
g-index

24
all docs

24
docs citations

24
times ranked

1079
citing authors

#	ARTICLE	IF	CITATIONS
1	Stable amorphous In ₂ O ₃ -based thin-film transistors by incorporating SiO ₂ to suppress oxygen vacancies. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	83
2	Carbon Nanosheets by Morphology-Retained Carbonization of Two-Dimensional Assembled Anisotropic Carbon Nanorings. <i>Angewandte Chemie - International Edition</i> , 2018, 57, 9679-9683.	7.2	80
3	Low-temperature processable amorphous In-W-O thin-film transistors with high mobility and stability. <i>Applied Physics Letters</i> , 2014, 104, 152103.	1.5	79
4	Robustness of Spin Polarization in Graphene-Based Spin Valves. <i>Advanced Functional Materials</i> , 2009, 19, 3711-3716.	7.8	70
5	Synthesis, properties, and crystal structures of π -extended double [6]helicenes: contorted multi-dimensional stacking lattice. <i>Organic and Biomolecular Chemistry</i> , 2017, 15, 4697-4703.	1.5	61
6	Dopant selection for control of charge carrier density and mobility in amorphous indium oxide thin-film transistors: Comparison between Si- and W-dopants. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	56
7	Photo-oxidation of Graphene in the Presence of Water. <i>Journal of Physical Chemistry C</i> , 2013, 117, 1453-1456.	1.5	45
8	Coexistence of Dirac-cone states and superconductivity in iron pnictide Ba(Fe _{1-x} Ru _x As) ₂ . <i>Physical Review B</i> , 2011, 84, .	1.1	27
9	Suppression of excess oxygen for environmentally stable amorphous In-Si-O thin-film transistors. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	25
10	Codoping of zinc and tungsten for practical high-performance amorphous indium-based oxide thin film transistors. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	23
11	Reduction of the interfacial trap density of indium-oxide thin film transistors by incorporation of hafnium and annealing process. <i>AIP Advances</i> , 2015, 5, .	0.6	16
12	Hole-transporting materials based on thiophene-fused arenes from sulfur-mediated thienannulations. <i>Materials Chemistry Frontiers</i> , 2018, 2, 275-280.	3.2	16
13	Perfluorocycloparaphenylenes. <i>Nature Communications</i> , 2022, 13, .	5.8	16
14	Self-formed copper oxide contact interlayer for high-performance oxide thin film transistors. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	13
15	Phase transitions from semiconductive amorphous to conductive polycrystalline in indium silicon oxide thin films. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	13
16	Gate-controlled ultraviolet photo-etching of graphene edges. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	12
17	Enhanced sensing response of oxidized graphene formed by UV irradiation in water. <i>Nanotechnology</i> , 2015, 26, 105701.	1.3	10
18	Analysis of Degradation in Graphene-Based Spin Valves. <i>Applied Physics Express</i> , 2009, 2, 123004.	1.1	9

#	ARTICLE	IF	CITATIONS
19	Controllable film densification and interface flatness for high-performance amorphous indium oxide based thin film transistors. Applied Physics Letters, 2014, 105, .	1.5	9
20	Gate-controlled photo-oxidation of graphene for electronic structure modification. Journal of Materials Chemistry C, 2019, 7, 1904-1912.	2.7	7
21	Spin injection and detection in a graphene lateral spin valve using an yttrium-oxide tunneling barrier. Applied Physics Express, 2014, 7, 085101.	1.1	6
22	Influence of Al ₂ O ₃ layer insertion on the electrical properties of Ga-In-Zn-O thin-film transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	6
23	Effect of carbon doping on threshold voltage and mobility of In-Si-O thin-film transistors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, 061206.	0.6	5
24	Correlation between active layer thickness and ambient gas stability in IGZO thin-film transistors. Journal Physics D: Applied Physics, 2017, 50, 025102.	1.3	4